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THIN FILM TRANSISTOR PANEL

Abstract

A thin film transistor panel includes a gate line with a gate electrode on a substrate, a gate insulating layer on the gate line, a semiconductor layer on the gate insulating layer, a conductive pattern layer with source and drain electrodes spaced apart on the semiconductor layer, a passivation layer on the semiconductor layer and the conductive pattern layer, and a plurality of pixel electrodes on the passivation layer. The thin film transistor panel is characterized in that the conductive pattern layer is formed from composite metallic layers including Mo/Ag-Al alloy/Mo. Furthermore, the gate line may be formed from a gate metal layer including an Ag-Al alloy layer and a molybdenum layer. The present invention further provides a sputtering target of Ag-Al alloy for forming the Ag-Al alloy layer.